

## ABSTRACT OF DISCLOSURE

In a thin film transistor having a semiconductor film provided above a substrate, a gate insulating film covering the semiconductor  
5 film, a gate electrode formed on the gate insulating film, and an interlayer insulating film covering the gate electrode, the gate electrode has a tapered shape wherein the width becomes wider from the side of the interlayer insulating film towards the gate insulating film. With this structure, the characteristics are stabilized. The  
10 electrode having a tapered shape can be formed through a first etching step wherein etching is applied to an electrode material layer to a degree where at least a portion of the electrode material layer remains and a second etching step wherein etching is applied to the electrode material layer while the mask is being ashed.